

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

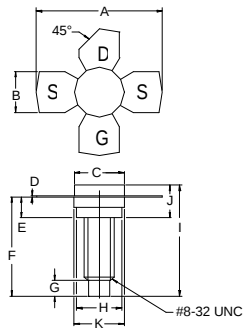
The ASI TVV005 is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	55 V
V_{CEO}	30 V
V_{EBO}	4.0 V
P_{DISS}	50 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	3.5°C/W

PACKAGE STYLE .280 4L STUD		
		
DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24
ORDER CODE: ASI10654		

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50\text{ mA}$	30			V
BV_{CER}	$I_C = 20\text{ mA}$ $R_{BE} = 10\ \Omega$	55			V
BV_{CBO}	$I_C = 20\text{ mA}$	55			V
BV_{EBO}	$I_E = 2.0\text{ mA}$	4.0			V
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$	10		---	---
C_{OB}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			35	pF
P_G	$V_{CE} = 28\text{ V}$ $P_{OUT} = 5.0\text{ W}$ $I_C = 1.0\text{ A}$ $f = 225\text{ MHz}$	15			dB
IMD_1	$V_{CE} = 28\text{ V}$ $P_{OUT} = 5.0\text{ W}$ $I_C = 1.0\text{ A}$ $f = 225\text{ MHz}$ Vision Carrier = -8 dB ref. Sound Carrier = -7 dB ref. Sideband Signal = -16 dB ref.	-55			dBc
ψ	$V_{CE} = 28\text{ V}$ $P_{OUT} = 5.0\text{ W}$ $I_C = 1.0\text{ A}$ $f = 225\text{ MHz}$ Load VSWR = $\infty:1$, All Phase Angles	No Degradation in Output Power			